TOSHIBA Transistor Silicon NPN Diffused Type (PCT process)

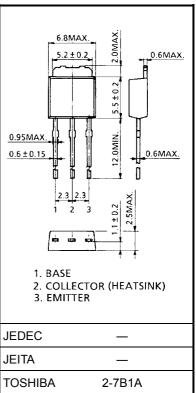
# 2SD1221

Audio Frequency Power Amplifier Application

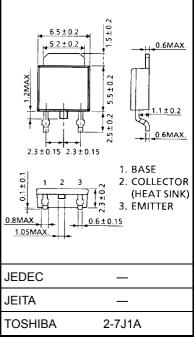
- Low collector saturation voltage
  - : VCE (sat) = 4.0 V (typ.) (IC = 3 A, IB = 0.3 A)
- High power dissipation: Pc = 20 W (Tc = 25°C)
- Complementary to 2SB906

## Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	60	V	
Collector-emitter voltage		V <sub>CEO</sub>	60	V	
Emitter-base voltage		V <sub>EBO</sub>	7	V	
Collector current		Ι <sub>C</sub>	3	А	
Base current		Ι <sub>Β</sub>	0.5	А	
Collector power dissipation	Ta = 25°C	Pc	1.0	W	
	Tc = 25°C	гC	20		
Junction temperature		Тj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



Weight: 0.36 g (typ.)



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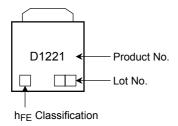
Unit: mm

**Electrical Characteristics (Ta = 25°C)** 

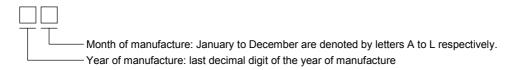
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I <sub>CBO</sub>	V <sub>CB</sub> = 60 V, I <sub>E</sub> = 0	_	_	100	μA
Emitter cut-off current		I <sub>EBO</sub>	V <sub>EB</sub> = 7 V, I <sub>C</sub> = 0	_	_	100	μA
Collector-emitter breakdown voltage		V (BR) CEO	I <sub>C</sub> = 50 mA, I <sub>B</sub> = 0	60	-	-	V
DC current gain		h <sub>FE (1)</sub> (Note)	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 0.5 A	60	_	300	
		h <sub>FE (2)</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 3 A	20	_	_	
Collector-emitter	saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 3 A, I <sub>B</sub> = 0.3 A	_	0.4	1.0	V
Base-emitter voltage		V <sub>BE</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 0.5 A	_	0.7	1.0	V
Transition frequency		fT	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 0.5 A	_	3.0	_	MHz
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz		70		pF
Switching time	Turn-on time	t <sub>on</sub>	$20 \ \mu s \qquad  B1 \qquad OUTPUT \\ INPUTo \qquad HB2 \qquad VCC = 30 \ V \\ I_{B1} = -I_{B2} = 0.2 \ A, \ DUTY \ CYCLE \le 1\%$	_	0.8	_	
	Storage time	t <sub>stg</sub>		_	1.5	_	μs
	Fall time	t <sub>f</sub>		_	0.8	_	

Note: hFE classification O: 60 to 120, Y: 100 to 200, GR: 150 to 300

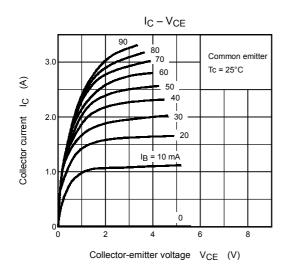
#### Marking

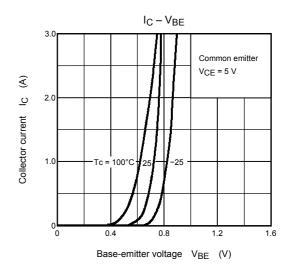


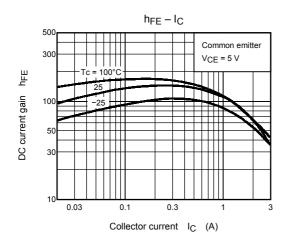
# Explanation of Lot No.

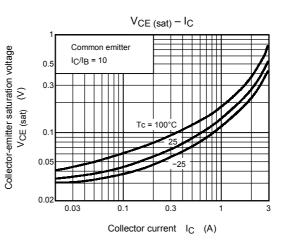


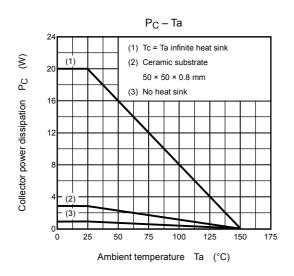
# **TOSHIBA**

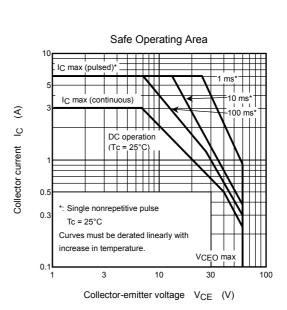












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